

AMENDMENTS TO THE SPECIFICATION

Page 4, please replace paragraph [0013] with the following:

[0013] According to embodiments of the invention, the gate affects the doped surface layer of the photodiode at least partially through a sidewall of the gate to reduce a potential barrier in a region where the gate and photodiode are in close proximity to one another. These and other features of the invention will be more apparent from the following detailed description that is provided in connection with the accompanying drawings.